

### **DCC010**

Sillicon Epitaxial Planar Type (Series Connection)

# **Ultrahigh-Speed Switching Diode**

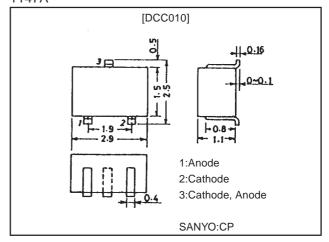
#### **Features**

- · Ideally suited for use in hybrid ICs because of very small package.
- · Fast switching speed.
- · Small interterminal capacitance.

### **Package Dimensions**

unit:mm

1147A



### **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

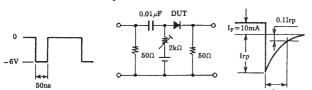
Symbol	Conditions	Ratings	Unit
V <sub>RM</sub>		85	V
VR		80	V
I <sub>FM</sub>	Unit Rating	300	mA
		210	mA
Io	Unit Rating	100	mA
		70	mA
I <sub>FSM</sub>	Unit Rating	4	Α
		2.8	Α
Р		200	mW
Tj		125	°C
Tstg		-55 to +125	°C
	V <sub>RM</sub> V <sub>R</sub> V <sub>R</sub> I <sub>FM</sub> I <sub>O</sub> I <sub>FSM</sub> P Tj	VRM VR IFM Unit Rating  IO Unit Rating  IFSM Unit Rating  P Tj	VRM         85           VR         80           IFM         Unit Rating         300           IO         Unit Rating         100           IFSM         Unit Rating         4           P         200           Tj         125

#### Electrical Characteristics at Ta = 25°C

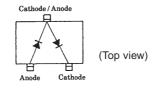
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Forward Voltage	V <sub>F</sub> (1)	I <sub>F</sub> =1mA		0.60		V
	V <sub>F</sub> (2)	I <sub>F</sub> =10mA		0.72		V
	V <sub>F</sub> (3)	I <sub>F</sub> =100mA			1.20	V
Reverse Current	I <sub>R</sub> (1)	V <sub>R</sub> =30V			0.1	μA
	I <sub>R</sub> (2)	V <sub>R</sub> =80V			0.5	μΑ
Interterminal Capacitance	С	V <sub>R</sub> =0V, f=1MHz			3.0	pF
Reverse Recovery Time	trr	I <sub>F</sub> =10mA, V <sub>R</sub> =6V, R <sub>L</sub> =50Ω, Irr=0.1Irp			4.0	ns

· Marking:W7

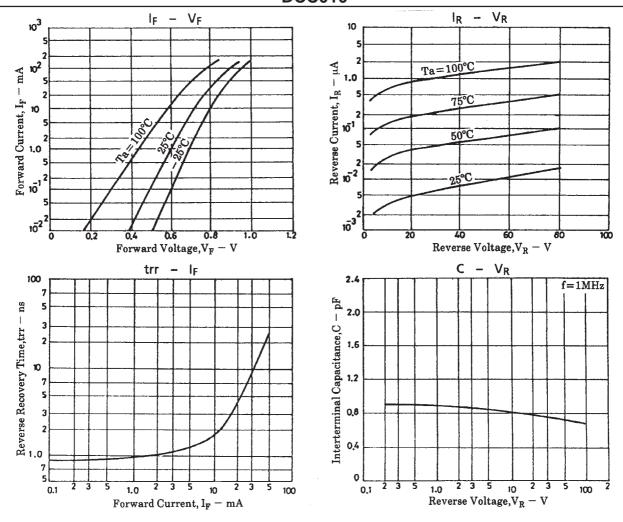
#### **Reverse Recovery Time Test Circuit**



#### **Electrical Connection**



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